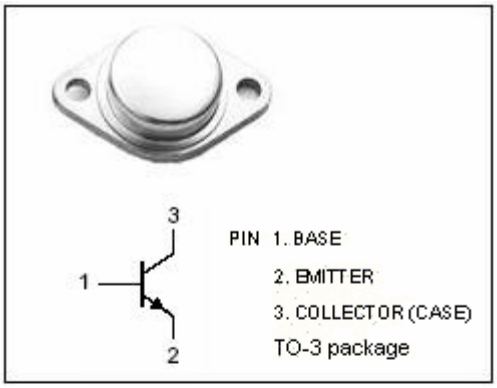
isc Silicon NPN Power Transistor BU108

DESCRIPTION

- High Voltage
- High Switching Speed
- Collector Current- I_C = 5A

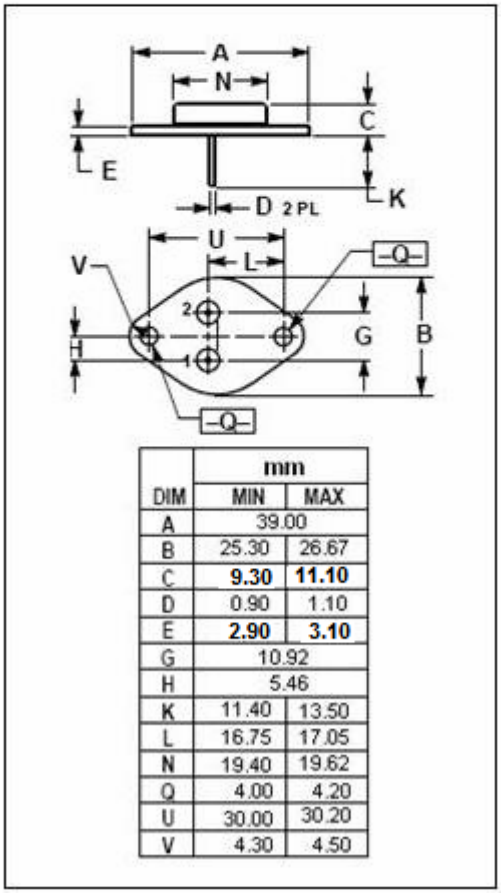


APPLICATIONS

- Designed for high voltage CRT scanning applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	750	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	5	A
I_B	Base Current-Continuous	3.5	A
I_E	Emitter Current-Continuous	8.5	A
P_C	Collector Power Dissipation @V_{CE}≤100V,T_C≤95℃	12.5	W
T_J	Junction Temperature	115	℃
T_{stg}	Storage Temperature	-65~115	℃



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	9.30	11.10
D	0.90	1.10
E	2.90	3.10
G	10.92	
H	5.46	
K	11.40	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.6	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 100mA ; I_C= 0	5		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 4.5A; I_B= 2A		5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 4.5A; I_B= 2A		1.3	V
I_{CEX}	Collector Cutoff Current	V_{CE}= 1500V; V_{BE}= -2V		1.0	mA
I_{CBO}	Collector Cutoff Current	V_{CB}= 1500V; I_E= 0		1.0	mA
h_{FE}	DC Current Gain	I_C= 1A ; V_{CE}= 5V	8		
t_f	Fall Time	I_C= 4.5A		1.2	μs